**Vishay Semiconductors** 

# Ultrafast Rectifier, 75 A FRED Pt<sup>®</sup>



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Base ca	athode
	2
	•
	<b>▲</b>
॑ 1 Cathode	් 3 Anode

PRODUCT SUMMARY								
Package	TO-247AD 2L							
I <sub>F(AV)</sub>	75 A							
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.95 V							
t <sub>rr</sub>	62 ns							
T <sub>J</sub> max.	175 °C							
Diode variation	Single die							

### **FEATURES**

- · Ultrafast and soft recovery time
- Optimized forward voltage drop
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Rugged design
- · Good thermal performance
- FREE · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, recovery time, and soft recovery. Polyimide passivated, planar structure and the platinum doped life time control guarantee, ruggedness, reliability characteristics, and solid value proposition for efficiency and thermal performance.

These devices are intended for use in boost stage in the AC/DC section of SMPS, high frequency output rectification of battery charger, inverters of solar inverters, or as freewheeling diodes in motor drive.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 140 °C, D = 0.50	75	
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_C$ = 25 °C, $t_p$ = 10 ms, sine wave	700	А
Repetitive peak forward current	I <sub>FRM</sub>		150	
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 1.5 mA	1200	-	-				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 75 A	-	2.05	2.55	V			
		I <sub>F</sub> = 75 A, T <sub>J</sub> = 125 °C	-	1.95	2.37				
Reverse leakage current		$V_R = V_R$ rated	-	-	420	μA			
neverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	875	μΑ			
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	90	-	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 10$	00 A/µs, V <sub>R</sub> = 30 V	-	62	-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	265	-	ns			
		T <sub>J</sub> = 125 °C		-	509	-				
Pools recovery ourrent	I <sub>RRM</sub>	$T_J = 25 \ ^\circ C$	l <sub>F</sub> = 50 A dl <sub>F</sub> /dt = 100 A/µs	-	10.4	-	A			
Peak recovery current		T <sub>J</sub> = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	19.2	-				
Devenue verse shares	0	T <sub>J</sub> = 25 °C		-	1390	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	4900	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	0.11	0.16				
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	31	36	°C/W			
Thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.23	0.5				
Weight			-	0.2	-	g			
Weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C			
Marking device		Case style: TO-247AD 2L		75EP	U12L				

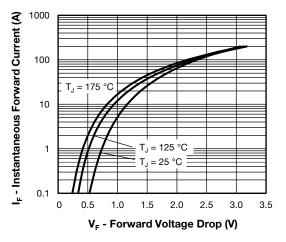


Fig. 1 - Typical Forward Voltage Drop Characteristics

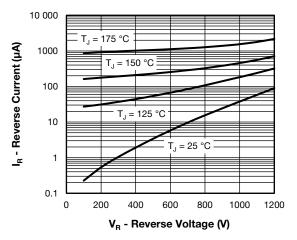


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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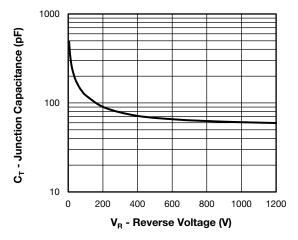


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

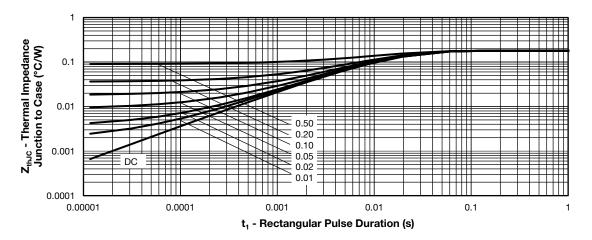


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

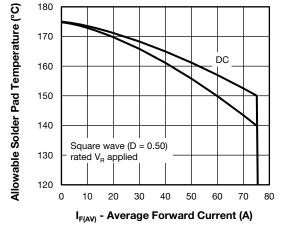


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

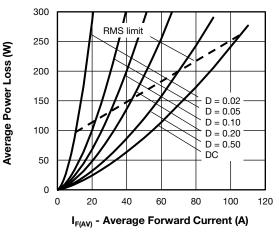


Fig. 6 - Forward Power Loss Characteristics

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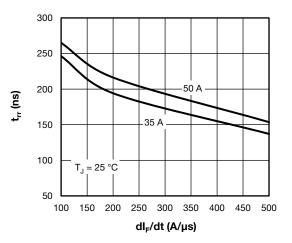
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VS-75EPU12L-N3

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Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

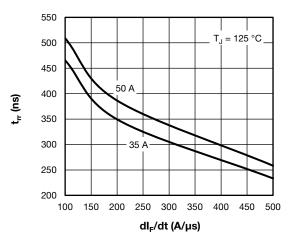


Fig. 8 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

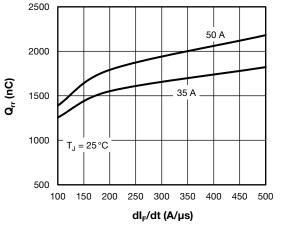


Fig. 9 - Typical Stored Charge vs. dl<sub>F</sub>/dt

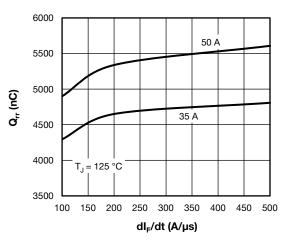


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

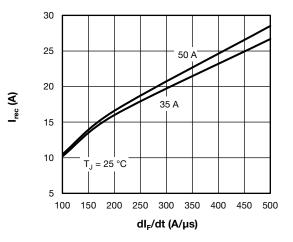


Fig. 11 - Typical Reverse Current vs. dl<sub>F</sub>/dt

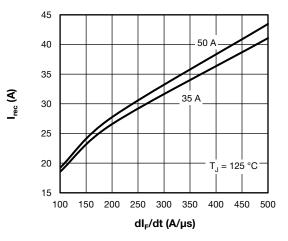


Fig. 12 - Typical Reverse Current vs. dI<sub>F</sub>/dt

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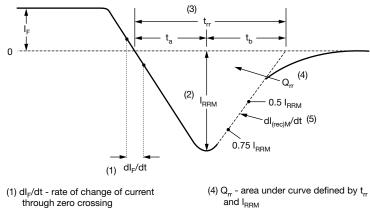
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## **VS-75EPU12L-N3**

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(2) I<sub>RRM</sub> - peak reverse recovery current

(3) t<sub>rr</sub> - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.

and I<sub>RRM</sub>

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ 

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 13 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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Device code	vs-	75	Е	Р	U	12	L	-N3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
	<u> </u>	Visł	nay Sem	niconduc	ctors pro	oduct	0	0
	2 -			ng (75 =	: 75 A)			
	3 - 4 -		single c kage:	liode				
			TO-247	,				
	5 -	U =	ultrafas	t recove	ery			
	6 -	Volt	age rati	ng (12 =	= 1200 \	/)		
	7 -	L =	long lea	lds				
	8 -	Env	ironmer	ntal digit	:			
		-N3	= halog	jen-free,	RoHS-	complia	int, and	totally I

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-75EPU12L-N3	25	500	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?95536							
Part marking information	www.vishay.com/doc?95648						

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**TO-247AD 2L** 

#### **DIMENSIONS** in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIN	MILLIMETERS		HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209		E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102		E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098		е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055		ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053		L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094		L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092		ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035		Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033		Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3	R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4	S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053			•		•		•

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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